

AMENDMENT TO THE CLAIMS

Claims 1-257 (canceled)

258. (previously presented) A memory element, comprising:
a first dielectric material having an opening;
a conductive material lining the sidewall surface of said opening;
a second dielectric material formed over said conductive material within said opening; and
a programmable resistance material electrically coupled to a top surface of said conductive material.

259. (previously presented) The memory element of claim 258, wherein said conductive material is at least one conductive sidewall spacer.

260. (currently amended) The memory element of claim 258, wherein said conductive material is formed over only a portion of the bottom surface of said opening, said portion being less than the entire bottom surface of said opening.

261. (previously presented) The memory element of claim 258, wherein said opening is a trench.

262. (previously presented) The memory element of claim 258, wherein said opening is a hole.

263. (previously presented) The memory element of claim 258, wherein said conductive material comprises at least one material selected from the group consisting of titanium nitride, titanium aluminum nitride, titanium carbonitride,

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titanium silicon nitride, carbon, N- doped polysilicon, titanium tungsten, tungsten silicide, tungsten, molybdenum, N+ doped polysilicon.

264. (previously presented) The memory element of claim 258, wherein said programmable resistance material includes a phase change material.

265. (previously presented) The memory element of claim 258, wherein said programmable resistance material includes a chalcogen element.

266. (previously presented) The memory element of claim 258, wherein said top surface is a top edge of said conductive material.

267. (previously presented) The memory element of claim 258, wherein said conductive material includes one or more protruding portions extending toward said programmable resistance material.

268. (previously presented) The memory element of claim 258, wherein said first dielectric material and said second dielectric material are formed of the same material.

Claims 269-275 (canceled)

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